

Norifumi Fujimura

List of Publications by Year in descending order

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164
papers

2,974
citations

257450

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50
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164
all docs

164
docs citations

164
times ranked

2462
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Control of preferred orientation for ZnOx films: control of self-texture. Journal of Crystal Growth, 1993, 130, 269-279. | 1.5 | 665 |
| 2 | Epitaxially grown YMnO3 film: New candidate for nonvolatile memory devices. Applied Physics Letters, 1996, 69, 1011-1013. | 3.3 | 303 |
| 3 | Ferroelectric properties of YMnO3 epitaxial films for ferroelectric-gate field-effect transistors. Journal of Applied Physics, 2003, 93, 5563-5567. | 2.5 | 105 |
| 4 | Growth mechanism of YMnO3 film as a new candidate for nonvolatile memory devices. Journal of Applied Physics, 1996, 80, 7084-7088. | 2.5 | 94 |
| 5 | Structural, dielectric, and magnetic properties of epitaxially grown BaFeO3 thin films on (100) SrTiO3 single-crystal substrates. Applied Physics Letters, 2002, 81, 2764-2766. | 3.3 | 89 |
| 6 | Characterization of ferroelectricity in metal/ferroelectric/insulator/semiconductor structure by pulsed C-V measurement; Ferroelectricity in YMnO3/Y2O3/Si structure. Journal of Applied Physics, 2000, 87, 3444-3449. | 2.5 | 72 |
| 7 | Direct piezoelectric properties of (100) and (111) BiFeO3 epitaxial thin films. Applied Physics Letters, 2012, 100, 102901. | 3.3 | 69 |
| 8 | Ferroelectric properties of c-oriented YMnO3 films deposited on Si substrates. Applied Physics Letters, 1998, 73, 414-416. | 3.3 | 60 |
| 9 | Raman scattering studies on multiferroic YMnO ₃ . Journal of Physics Condensed Matter, 2007, 19, 365239. | 1.8 | 55 |
| 10 | Ferroelectricity of YMnO3 thin films prepared via solution. Applied Physics Letters, 1999, 75, 719-721. | 3.3 | 54 |
| 11 | Formation of two-dimensional electron gas and the magnetotransport behavior of ZnMnO/ZnO heterostructure. Journal of Applied Physics, 2003, 93, 7673-7675. | 2.5 | 53 |
| 12 | Ferromagnetic and ferroelectric behaviors of A-site substituted YMnO3-based epitaxial thin films. Journal of Applied Physics, 2003, 93, 6990-6992. | 2.5 | 44 |
| 13 | Magnetic properties of highly resistive BaFeO3 thin films epitaxially grown on SrTiO3 single-crystal substrates. Journal of Applied Physics, 2003, 93, 6993-6995. | 2.5 | 40 |
| 14 | LiNbO3 film with a new epitaxial orientation on R-cut sapphire. Journal of Applied Physics, 1994, 75, 2169-2176. | 2.5 | 37 |
| 15 | Piezoelectric Vibrational Energy Harvester Using Lead-Free Ferroelectric BiFeO ₃ Films. Applied Physics Express, 2013, 6, 051501. | 2.4 | 37 |
| 16 | Effect of Oxygen Deficiencies on Magnetic Properties of Epitaxial Grown BaFeO_{3-x} Thin Films on. IEEE Transactions on Magnetics, 2004, 40, 2736-2738. | 2.1 | 35 |
| 17 | Electrical Characteristics of Controlled-Polarization-Type Ferroelectric-Gate Field-Effect Transistor. Japanese Journal of Applied Physics, 2008, 47, 8874. | 1.5 | 35 |
| 18 | Influence of Schottky and Poole-Frenkel emission on the retention property of YMnO3-based metal/ferroelectric/insulator/semiconductor capacitors. Journal of Applied Physics, 2003, 94, 4036-4041. | 2.5 | 34 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 19 | Improvement of magnetization and leakage current properties of magnetoelectric BaFeO ₃ thin films by Zr substitution. Applied Physics Letters, 2005, 86, 082902. | 3.3 | 33 |
| 20 | Influence of antiferromagnetic exchange interaction on magnetic properties of ZnMnO thin films grown pseudomorphically on ZnO (0001Å ⁻¹) single-crystal substrates. Journal of Applied Physics, 2008, 103, . | 2.5 | 33 |
| 21 | The effects of Xe on an rf plasma and growth of ZnO films by rf sputtering. Journal of Applied Physics, 2004, 95, 3923-3927. | 2.5 | 32 |
| 22 | Pulsed-Laser-Deposited YMnO ₃ Epitaxial Films with Square Polarization-Electric Field Hysteresis Loop and Low-Temperature Growth. Japanese Journal of Applied Physics, 2004, 43, 6613-6616. | 1.5 | 31 |
| 23 | Systematic Study of Photoluminescence Enhancement in Monolayer Molybdenum Disulfide by Acid Treatment. Langmuir, 2018, 34, 10243-10249. | 3.5 | 29 |
| 24 | Effect of substitutionally dissolved Ce in Si on the magnetic and electric properties of magnetic semiconductor Si _{1-x} Ce _x films. Applied Physics Letters, 2002, 81, 4023-4025. | 3.3 | 28 |
| 25 | Epitaxial growth of CuScO ₂ thin films on sapphire a-plane substrates by pulsed laser deposition. Journal of Applied Physics, 2005, 97, 083535. | 2.5 | 25 |
| 26 | Photoluminescence properties peculiar to the Mn-related transition in a lightly alloyed ZnMnO thin film grown by pulsed laser deposition. Applied Physics Letters, 2006, 88, 241908. | 3.3 | 24 |
| 27 | Photoactivation of Strong Photoluminescence in Superacid-Treated Monolayer Molybdenum Disulfide. ACS Applied Materials & Interfaces, 2020, 12, 36496-36504. | 8.0 | 24 |
| 28 | Detailed structural analysis of Ce doped Si thin films. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 237-241. | 2.7 | 22 |
| 29 | Microstructure and Dielectric Properties of YMnO ₃ Thin Films Prepared by Dip-Coating. Journal of the American Ceramic Society, 1998, 81, 1357-1360. | 3.8 | 20 |
| 30 | Multiferroic behaviour of YMnO ₃ and YbMnO ₃ epitaxial films. Philosophical Magazine Letters, 2007, 87, 193-201. | 1.2 | 20 |
| 31 | Analysis of nitrogen plasma generated by a pulsed plasma system near atmospheric pressure. Journal of Applied Physics, 2004, 96, 6094-6096. | 2.5 | 19 |
| 32 | Development of Piezoelectric MEMS Vibration Energy Harvester Using (100) Oriented BiFeO ₃ Ferroelectric Film. Journal of Physics: Conference Series, 2013, 476, 012007. | 0.4 | 19 |
| 33 | Enhancement of piezoelectric properties of (100)-orientated BiFeO ₃ films on (100)LaNiO ₃ /Si. Japanese Journal of Applied Physics, 2014, 53, 09PA14. | 1.5 | 19 |
| 34 | Strain Dependent Electronic Structure and Band Offset Tuning at Heterointerfaces of A ₂ SnO ₃ (A=Ca, Sr, Ba). Applied Physics Letters, 2010, 96, 082101. | 3.3 | 19 |
| 35 | Demonstration of high-performance piezoelectric MEMS vibration energy harvester using BiFeO ₃ film with improved electromechanical coupling factor. Sensors and Actuators A: Physical, 2019, 291, 167-173. | 4.1 | 19 |
| 36 | Electro-optical effect in ZnO:Mn thin films prepared by Xe sputtering. Journal of Applied Physics, 2006, 99, 013509. | 2.5 | 18 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 37 | Time-Dependent Imprint in $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ Ferroelectric Thin Films. <i>Advanced Electronic Materials</i> , 2021, 7, 2100151. | 5.1 | 18 |
| 38 | Electro-Optic Effect in Epitaxial ZnO:Mn Thin Films. <i>Japanese Journal of Applied Physics</i> , 2002, 41, 6916-6918. | 1.5 | 17 |
| 39 | Reaction of Si with excited nitrogen species in pure nitrogen plasma near atmospheric pressure. <i>Thin Solid Films</i> , 2006, 506-507, 423-426. | 1.8 | 16 |
| 40 | Preparation and Dielectric Properties of YMnO_3 Ferroelectric Thin Films by the Sol-Gel Method. <i>Journal of Sol-Gel Science and Technology</i> , 1998, 13, 903-908. | 2.4 | 15 |
| 41 | Preparation and the magnetic property of ZnMnO thin films on ZnO single crystal substrate. <i>Journal of Magnetism and Magnetic Materials</i> , 2007, 310, e711-e713. | 2.3 | 15 |
| 42 | Electromechanical characteristics of piezoelectric vibration energy harvester with 2-degree-of-freedom system. <i>Applied Physics Letters</i> , 2019, 114, . | 3.3 | 15 |
| 43 | Effect of carrier for magnetic and magnetotransport properties of Si:Ce films. <i>Journal of Applied Physics</i> , 2003, 93, 7679-7681. | 2.5 | 14 |
| 44 | Magnetic and magnetotransport properties of solid phase epitaxially grown Si:Ce films. <i>Journal of Applied Physics</i> , 2003, 93, 4045-4048. | 2.5 | 14 |
| 45 | Electro-optic effect in ZnO:Mn thin films. <i>Journal of Alloys and Compounds</i> , 2004, 371, 157-159. | 5.5 | 14 |
| 46 | Detailed structural analysis and dielectric properties of silicon nitride film fabricated using pure nitrogen plasma generated near atmospheric pressure. <i>Journal of Applied Physics</i> , 2006, 100, 073710. | 2.5 | 14 |
| 47 | Analysis of carrier modulation in channel of ferroelectric-gate transistors having polar semiconductor. <i>Thin Solid Films</i> , 2010, 518, 3026-3029. | 1.8 | 14 |
| 48 | Impedance Analysis of Controlled-Polarization-Type Ferroelectric-Gate Thin Film Transistor Using Resistor-Capacitor Lumped Constant Circuit. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DD16. | 1.5 | 14 |
| 49 | Synthesis of $\text{Bi}(\text{Fe}_x\text{Al}_{1-x})\text{O}_3$ Thin Films by Pulsed Laser Deposition and Its Structural Characterization. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 6609-6612. | 1.5 | 13 |
| 50 | Ferromagnetic and dielectric behavior of mn-doped BaCoO_3 . <i>IEEE Transactions on Magnetics</i> , 2005, 41, 3496-3498. | 2.1 | 13 |
| 51 | Growth and Ferromagnetic Properties of Ferroelectric YbMnO_3 Thin Films. <i>Japanese Journal of Applied Physics</i> , 2006, 45, 7329-7331. | 1.5 | 12 |
| 52 | Magnetic frustration behavior of ferroelectric ferromagnet YbMnO_3 epitaxial films. <i>Journal of Applied Physics</i> , 2007, 101, 09M107. | 2.5 | 12 |
| 53 | Polarization Switching Behavior of YMnO_3 Thin Film at around Magnetic Phase Transition Temperature. <i>Japanese Journal of Applied Physics</i> , 2009, 48, 09KB05. | 1.5 | 12 |
| 54 | Title is missing!. <i>Journal of Sol-Gel Science and Technology</i> , 2000, 19, 589-593. | 2.4 | 11 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 55 | Ce concentration dependence on the magnetic and transport properties of Ce doped Si epitaxial films prepared by molecular beam epitaxy. Journal of Applied Physics, 2002, 91, 7905. | 2.5 | 11 |
| 56 | Piezoelectric properties of (100) orientated BiFeO ₃ thin films on LaNiO ₃ . Japanese Journal of Applied Physics, 2014, 53, 08NB02. | 1.5 | 11 |
| 57 | Enhancement of ferromagnetic ordering in dielectric BaFe _{1-x} Zr _x O ₃ (x=0.5~0.8) single-crystal films by pulsed laser-beam deposition. Journal of Applied Physics, 2005, 97, 10M509. | 2.5 | 10 |
| 58 | Magnetic properties of low-temperature grown Si:Ce thin films on (001) Si substrate. Journal of Magnetism and Magnetic Materials, 2007, 310, e726-e728. | 2.3 | 10 |
| 59 | Contribution of s-d exchange interaction to magnetoresistance of ZnO-based heterostructures with a magnetic barrier. Physical Review B, 2009, 80, . | 3.2 | 10 |
| 60 | Enhancement of Direct Piezoelectric Properties of Domain-Engineered (100) BiFeO ₃ Films. Japanese Journal of Applied Physics, 2013, 52, 09KA03. | 1.5 | 10 |
| 61 | Correlation between the intra-atomic Mn ³⁺ photoluminescence and antiferromagnetic transition in an YMnO ₃ epitaxial film. Applied Physics Express, 2014, 7, 023002. | 2.4 | 10 |
| 62 | Piezoelectric energy harvesting from AC current-carrying wire. Japanese Journal of Applied Physics, 2019, 58, SLLD10. | 1.5 | 10 |
| 63 | Exotic Doping for ZnO Thin Films: Possibility of Monolithic Optical Integrated Circuit. Materials Research Society Symposia Proceedings, 1999, 574, 317. | 0.1 | 9 |
| 64 | Structural analysis and electrical properties of pure Ge ₃ N ₄ dielectric layers formed by an atmospheric-pressure nitrogen plasma. Journal of Applied Physics, 2011, 110, 064103. | 2.5 | 9 |
| 65 | Lowering the growth temperature of strongly-correlated YbFe ₂ O ₄ thin films prepared by pulsed laser deposition. Thin Solid Films, 2016, 614, 44-46. | 1.8 | 9 |
| 66 | Investigation of mechanical nonlinear effect in piezoelectric MEMS vibration energy harvesters. Japanese Journal of Applied Physics, 2018, 57, 11UD03. | 1.5 | 9 |
| 67 | Growth process observation of homoepitaxial ZnO thin films using optical emission spectra during pulsed laser deposition. Thin Solid Films, 2010, 518, 2971-2974. | 1.8 | 8 |
| 68 | Interface energetics and atomic structure of epitaxial La _{1-x} Sr _x CoO ₃ on Nb:SrTiO ₃ . Applied Physics Letters, 2015, 106, . | 3.3 | 8 |
| 69 | The effects of small amounts of oxygen during deposition on structural changes in sputtered HfO ₂ -based films. Japanese Journal of Applied Physics, 2019, 58, SLLB03. | 1.5 | 8 |
| 70 | Ultralarge Photoluminescence Enhancement of Monolayer Molybdenum Disulfide by Spontaneous Superacid Nanolayer Formation. ACS Applied Materials & Interfaces, 2021, 13, 25280-25289. | 8.0 | 8 |
| 71 | Formation of Silicon Oxynitride Films with Low Leakage Current Using N ₂ /O ₂ Plasma near Atmospheric Pressure. Japanese Journal of Applied Physics, 2004, 43, 7853-7856. | 1.5 | 7 |
| 72 | Optical propagation loss of ZnO films grown on sapphire. Journal of Applied Physics, 2004, 95, 1673-1676. | 2.5 | 7 |

| # | ARTICLE | IF | CITATIONS |
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| 73 | Spin-dependent transport in a ZnMnO ₂ /ZnO heterostructure. Journal of Applied Physics, 2008, 103, 07D124. | 2.5 | 7 |
| 74 | Magnetic Properties of Uniformly Ce-Doped Si Thin Films with n-Type Conduction. Japanese Journal of Applied Physics, 2009, 48, 033003. | 1.5 | 7 |
| 75 | Surface preparation of ZnO single-crystal substrate for the epitaxial growth of ZnO thin films. Journal of Crystal Growth, 2011, 318, 516-518. | 1.5 | 7 |
| 76 | Evaluation of the electronic states in highly Ce doped Si films grown by low temperature molecular beam epitaxy system. Journal of Crystal Growth, 2015, 425, 158-161. | 1.5 | 7 |
| 77 | Growth and ferroelectric properties of La and Al codoped BiFeO ₃ epitaxial films. Journal of Applied Physics, 2017, 121, 174102. | 2.5 | 7 |
| 78 | Effect of Additional Oxygen on Formation of Silicon Oxynitride Using Nitrogen Plasma Generated near Atmospheric Pressure. Japanese Journal of Applied Physics, 2006, 45, 9025-9028. | 1.5 | 6 |
| 79 | Influence of antiferromagnetic ordering on ferroelectric polarization switching of YMnO ₃ /epitaxial thin films. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2007, 54, 2641-2644. | 3.0 | 6 |
| 80 | The comparison of the growth models of silicon nitride ultrathin films fabricated using atmospheric pressure plasma and radio frequency plasma. Journal of Applied Physics, 2007, 101, 023513. | 2.5 | 6 |
| 81 | Low temperature growth of Si:Ce thin films with high crystallinity and uniform distribution of Ce grown by solid-source molecular beam epitaxy. Journal of Crystal Growth, 2007, 307, 30-34. | 1.5 | 6 |
| 82 | Electron transport properties of Zn _{0.88} Mn _{0.12} O ₂ /ZnO modulation-doped heterostructures. Journal of Vacuum Science & Technology B, 2009, 27, 1760. | 1.3 | 6 |
| 83 | Impedance Analysis of Controlled-Polarization-Type Ferroelectric-Gate Thin Film Transistor Using Resistor-Capacitor Lumped Constant Circuit. Japanese Journal of Applied Physics, 2011, 50, 04DD16. | 1.5 | 6 |
| 84 | Effect of the annealing temperature of P(VDF/TrFE) thin films on their ferroelectric properties. Journal of the Korean Physical Society, 2013, 62, 1065-1068. | 0.7 | 6 |
| 85 | Ultrafast dynamics of coherent optical phonon correlated with the antiferromagnetic transition in a hexagonal YMnO ₃ epitaxial film. Applied Physics Letters, 2017, 111, . | 3.3 | 6 |
| 86 | Investigation of the wake-up process and time-dependent imprint of Hf _{0.5} Zr _{0.5} O ₂ film through the direct piezoelectric response. Applied Physics Letters, 2021, 119, . | 3.3 | 6 |
| 87 | Investigation of efficient piezoelectric energy harvesting from impulsive force. Japanese Journal of Applied Physics, 2020, 59, SPPD04. | 1.5 | 6 |
| 88 | Effect of Ferroelectric Polarization on Carrier Transport in Controlled Polarization-Type Ferroelectric Gate Field-Effect Transistors with Poly(vinylidene fluoride-tetrafluoroethylene)/ZnO Heterostructure. Japanese Journal of Applied Physics, 2012, 51, 11PB01. | 1.5 | 6 |
| 89 | Orientation control of (Ca,Sr)CuO ₂ thin films. Journal of Applied Physics, 1995, 77, 3805-3811. | 2.5 | 5 |
| 90 | Dielectric properties of ferroelectric/DMS heterointerface using YMnO ₃ and Ce doped Si. Applied Surface Science, 2008, 254, 6218-6221. | 6.1 | 5 |

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|-----|--|-----|-----------|
| 91 | Aluminum-doped zinc oxide electrode for robust (Pb,La)(Zr,Ti)O ₃ capacitors: effect of oxide insulator encapsulation and oxide buffer layer. <i>Journal of Materials Science: Materials in Electronics</i> , 2014, 25, 2155-2161. | 2.2 | 5 |
| 92 | Al:ZnO top electrodes deposited with various oxygen pressures for ferroelectric (Pb,La)(Zr,Ti)O ₃ capacitors. <i>Electronics Letters</i> , 2016, 52, 230-232. | 1.0 | 5 |
| 93 | The effect of crystal distortion and domain structure on piezoelectric properties of BiFeO ₃ thin films. <i>Japanese Journal of Applied Physics</i> , 2018, 57, 11UF07. | 1.5 | 5 |
| 94 | Valence states and the magnetism of Eu ions in Eu-doped GaN. <i>Journal of Applied Physics</i> , 2020, 127, 083901. | 2.5 | 5 |
| 95 | Control of Crystal Structure of BiFeO ₃ Epitaxial Thin Films by Adjusting Growth Conditions and Piezoelectric Properties. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 09LB04. | 1.5 | 5 |
| 96 | Dissolution pits and Si epitaxial regrowth in the Al/(111)Si system. <i>Journal of Applied Physics</i> , 1988, 64, 4499-4502. | 2.5 | 4 |
| 97 | Magnetic and Ferroelectric Properties of YMnO ₃ Epitaxial Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 2006, 966, 1. | 0.1 | 4 |
| 98 | The effects of aluminum doping for the magnetotransport property of Si:Ce thin films. <i>Journal of Applied Physics</i> , 2010, 107, 09C308. | 2.5 | 4 |
| 99 | Orientation Control of ZnO Films Deposited Using Nonequilibrium Atmospheric Pressure N ₂ /O ₂ Plasma. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 01AC03. | 1.5 | 4 |
| 100 | Improved reliability properties of (Pb,La)(Zr,Ti)O ₃ ferroelectric capacitors by thin aluminium-doped zinc oxide buffer layer. <i>Electronics Letters</i> , 2014, 50, 799-801. | 1.0 | 4 |
| 101 | Near-surface structure of polar ZnO surfaces prepared by pulsed laser deposition. <i>Thin Solid Films</i> , 2014, 559, 88-91. | 1.8 | 4 |
| 102 | Crystallographic polarity effect of ZnO on thin film growth of pentacene. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 04CJ03. | 1.5 | 4 |
| 103 | Reaction of N,N-dimethylformamide and divalent viologen molecule to generate an organic dopant for molybdenum disulfide. <i>AIP Advances</i> , 2018, 8, 055313. | 1.3 | 4 |
| 104 | Quantitative analysis of the direct piezoelectric response of bismuth ferrite films by scanning probe microscopy. <i>Scientific Reports</i> , 2019, 9, 19727. | 3.3 | 4 |
| 105 | Change in the defect structure of composition controlled single-phase YbFe ₂ O ₄ epitaxial thin films. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SPPB07. | 1.5 | 4 |
| 106 | Structural control of nonequilibrium WSi _{2.6} thin films by external stress. <i>Journal of Applied Physics</i> , 1993, 73, 733-739. | 2.5 | 3 |
| 107 | Mechanism for ordering in SiGe films with reconstructed surface. <i>Applied Physics Letters</i> , 1997, 71, 1174-1176. | 3.3 | 3 |
| 108 | YMnO ₃ and YbMnO ₃ Thin Films for fet type FeRam Application. <i>Materials Research Society Symposia Proceedings</i> , 1999, 574, 237. | 0.1 | 3 |

| # | ARTICLE | IF | CITATIONS |
|-----|--|------|-----------|
| 109 | Origin of Leakage Current of YMnO ₃ Thin Films Prepared by the Sol-Gel Method. Materials Research Society Symposia Proceedings, 1999, 596, 481. | 0.1 | 3 |
| 110 | Effect of plasma-induced damage on interfacial reactions of titanium thin films on silicon surfaces. Applied Physics Letters, 2000, 76, 2358-2360. | 3.3 | 3 |
| 111 | Effects of spontaneous and piezoelectric polarizations on carrier confinement at the Zn _{0.88} Mn _{0.12} O/ZnO interface. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3107-3109. | 0.8 | 3 |
| 112 | Novel chemical vapor deposition process of ZnO films using nonequilibrium N ₂ plasma generated near atmospheric pressure with small amount of O ₂ below 1%. Journal of Applied Physics, 2016, 119, 175302. | 2.5 | 3 |
| 113 | Reliability of the Properties of (Pb,La)(Zr,Ti)O ₃ Capacitors with Non-noble Metal Oxide Electrodes stored in an H ₂ Atmosphere. MRS Advances, 2016, 1, 369-374. | 0.9 | 3 |
| 114 | Tuning Transition-Metal Dichalcogenide Field-Effect Transistors by Spontaneous Pattern Formation of an Ultrathin Molecular Dopant Film. ACS Nano, 2018, 12, 10123-10129. | 14.6 | 3 |
| 115 | Electronic Structure Mosaicity of Monolayer Transition Metal Dichalcogenides by Spontaneous Pattern Formation of Donor Molecules. ACS Applied Materials & Interfaces, 2019, 11, 15922-15926. | 8.0 | 3 |
| 116 | Time-resolved simulation of the negative capacitance stage emerging at the ferroelectric/semiconductor hetero-junction. AIP Advances, 2019, 9, 025037. | 1.3 | 3 |
| 117 | Metallic Transport in Monolayer and Multilayer Molybdenum Disulfides by Molecular Surface Charge Transfer Doping. ACS Applied Materials & Interfaces, 2022, , . | 8.0 | 3 |
| 118 | Solid phase reactions and change in stress of TiN/Ti/Si for a diffusion barrier. Journal of Applied Physics, 1990, 67, 2899-2903. | 2.5 | 2 |
| 119 | Formation of (1120) ZnO Films by Controlling the Selftexture and the Relaxation of Film Stress. Materials Research Society Symposia Proceedings, 1992, 263, 297. | 0.1 | 2 |
| 120 | The Progress of YMnO ₃ /Y ₂ O ₃ /Si System for a Ferroelectric Gate Field Effect Transistor. Ferroelectrics, 2002, 271, 229-234. | 0.6 | 2 |
| 121 | Magnetic and dielectric properties of Yb(Mn _{1-x} Al _x)O ₃ thin films. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2008, 55, 1056-1060. | 3.0 | 2 |
| 122 | Effects of La substitution for BiFeO ₃ epitaxial thin films. Journal of the Korean Physical Society, 2013, 62, 1069-1072. | 0.7 | 2 |
| 123 | Fabrication and Characterization of (Ba,La)SnO ₃ Semiconducting Epitaxial Films on (111) and (001) SrTiO ₃ Substrates. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1700800. | 1.8 | 2 |
| 124 | Strong Photoluminescence Enhancement from Bilayer Molybdenum Disulfide via the Combination of UV Irradiation and Superacid Molecular Treatment. Applied Sciences (Switzerland), 2021, 11, 3530. | 2.5 | 2 |
| 125 | Ce-Induced Reconstruction of Si(001) Surface Structures. Japanese Journal of Applied Physics, 2011, 50, 065701. | 1.5 | 2 |
| 126 | Detailed C-V Analysis for YbMnO ₃ /Y ₂ O ₃ /Si Structure. Materials Research Society Symposia Proceedings, 1999, 574, 359. | 0.1 | 1 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|-----|-----------|
| 127 | The Effect of Leakage Current on the Retention Property of YMnO ₃ Based MFIS Capacitor. Integrated Ferroelectrics, 2002, 49, 41-49. | 0.7 | 1 |
| 128 | Interface characteristics of (Zn,Mn)O/ZnO grown on ZnO substrate. Journal of Crystal Growth, 2005, 275, e2211-e2215. | 1.5 | 1 |
| 129 | Influence of Antiferromagnetic Ordering on Ferroelectric Polarization Switching of YMnO ₃ ; Epitaxial Thin Films. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , . | 0.0 | 1 |
| 130 | Electro-optic property of ZnO:Mn epitaxial films. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3110-3112. | 0.8 | 1 |
| 131 | Ferroelectric Properties of Magnetoferroelectric YMnO ₃ Epitaxial Films at around the Neel Temperature. Key Engineering Materials, 2010, 445, 144-147. | 0.4 | 1 |
| 132 | Effect of Lattice Misfit Strain on Crystal System and Ferroelectric Property of BiFeO ₃ Epitaxial Thin Films. IOP Conference Series: Materials Science and Engineering, 2011, 18, 092064. | 0.6 | 1 |
| 133 | Electronic Transport in Organic Ferroelectric Gate Field-Effect Transistors with ZnO Channel. Materials Research Society Symposia Proceedings, 2012, 1430, 19. | 0.1 | 1 |
| 134 | Effects of polarization of polar semiconductor on electrical properties of poly(vinylidene fluoride)/ferroelectric thin film heterostructure. Journal of Applied Physics, 2010, 108, 462-462. | 2.5 | 1 |
| 135 | Low temperature formation of highly resistive ZnO films using nonequilibrium N ₂ /O ₂ plasma generated near atmospheric pressure. Thin Solid Films, 2016, 616, 415-418. | 1.8 | 1 |
| 136 | Cerium ion doping into self-assembled Ge using three-dimensional dot structure. Journal of Crystal Growth, 2017, 468, 696-700. | 1.5 | 1 |
| 137 | High efficiency piezoelectric MEMS vibrational energy harvesters using (100) oriented BiFeO ₃ films. , 2017, , . | | 1 |
| 138 | Fabrication of chemical composition controlled YbFe ₂ O ₄ epitaxial thin films. Japanese Journal of Applied Physics, 2019, 58, SLLB11. | 1.5 | 1 |
| 139 | Correlation between photoluminescence and antiferromagnetic spin order in strongly correlated YMnO ₃ ferroelectric epitaxial thin film. AIP Advances, 2021, 11, 075122. | 1.3 | 1 |
| 140 | Fabrication of YMnO ₃ Films: New Candidate for Non-Volatile Memory Devices. Materials Research Society Symposia Proceedings, 1996, 433, 119. | 0.1 | 0 |
| 141 | Effect of carrier concentration on the magnetic behavior of ferroelectric YMnO ₃ ceramics and thin films. , 0, , . | | 0 |
| 142 | Effect of A-site substitution on the magnetic and dielectric behaviors of YMnO ₃ based ferroelectric thin films. , 0, , . | | 0 |
| 143 | Investigation of Retention Properties for YMnO ₃ Based Metal/Ferroelectric/Insulator/Semiconductor Capacitors. Materials Research Society Symposia Proceedings, 2003, 784, 971. | 0.1 | 0 |
| 144 | Investigation of Retention Properties for YMnO ₃ Based Metal/Ferroelectric/Insulator/Semiconductor Capacitors. Materials Research Society Symposia Proceedings, 2003, 786, 971. | 0.1 | 0 |

| # | ARTICLE | IF | CITATIONS |
|-----|---|-----|-----------|
| 145 | Fabrication of Silicon Nitride Film using Pure Nitrogen Plasma Generated near Atmospheric Pressure for III-V Semiconductor Fabrication. Materials Research Society Symposia Proceedings, 2004, 831, 144. | 0.1 | 0 |
| 146 | Magnetic properties of low temperature grown Si:Ce thin films on [001] Si substrate by molecular beam epitaxy. , 2005, , . | | 0 |
| 147 | Ferromagnetic and dielectric behavior of Mn doped BaCoO/sub 3/. , 2005, , . | | 0 |
| 148 | Magnetic properties of Er,O-codoped GaAs at low temperature. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4082-4085. | 0.8 | 0 |
| 149 | CaBi4Ti4O15 thin film deposition on electroplated Platinum substrates using a sol-gel method. Materials Research Society Symposia Proceedings, 2008, 1113, 1. | 0.1 | 0 |
| 150 | Dielectric Behavior of YMnO₃; Epitaxial Thin Film at around Magnetic Phase Transition Temperature. Advances in Science and Technology, 0, , . | 0.2 | 0 |
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